

LN2685LT1G

60V N-Channel (D-S) MOSFET

1. FEATURES

- $V_{DS} = 60V$.
- $R_{DS(ON)}, V_{GS}@10V \leq 75m\Omega$.
- $R_{DS(ON)}, V_{GS}@5V \leq 90m\Omega$.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.

2. APPLICATIONS

- Load/Power switch for portables and computing

3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LN2685LT1G	N85	3000/Tape&Reel

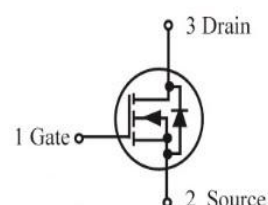
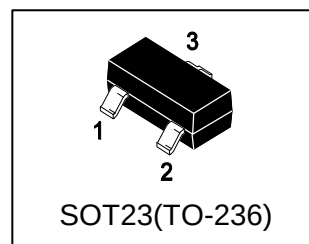
4. MAXIMUM RATINGS($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-to-Source Voltage – Continuous	V_{GS}	± 20	V
Drain Current			
– Continuous $T_a = 25^\circ C$	I_D	3	A
– Pulsed (Note 1)	I_{DM}	12	

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Maximum Power Dissipation	PD	1.25	W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	$^\circ C/W$
Junction and Storage temperature	T_J, T_{stg}	$-55 \sim +150$	$^\circ C$

1. Repetitive Rating: Pulse width limited by the Maximum junction temperature.
2. 1-in² 2oz Cu PCB board.

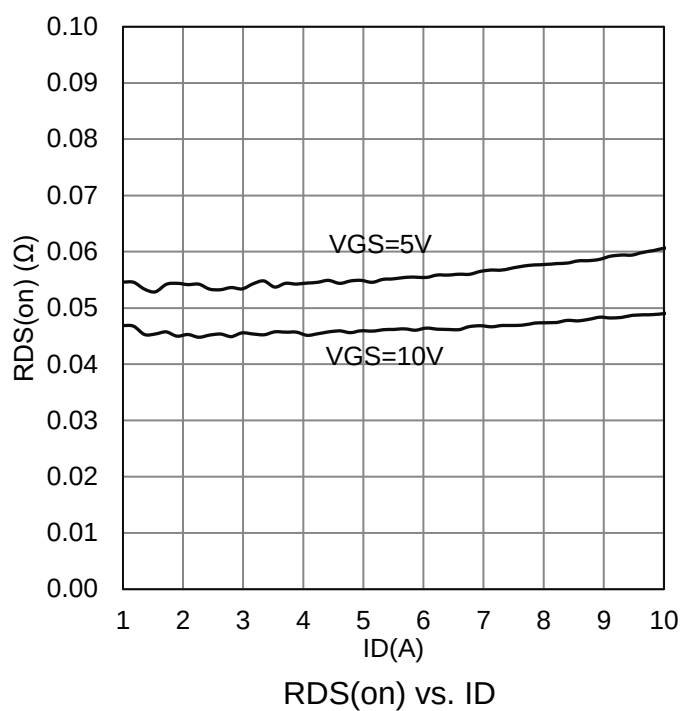
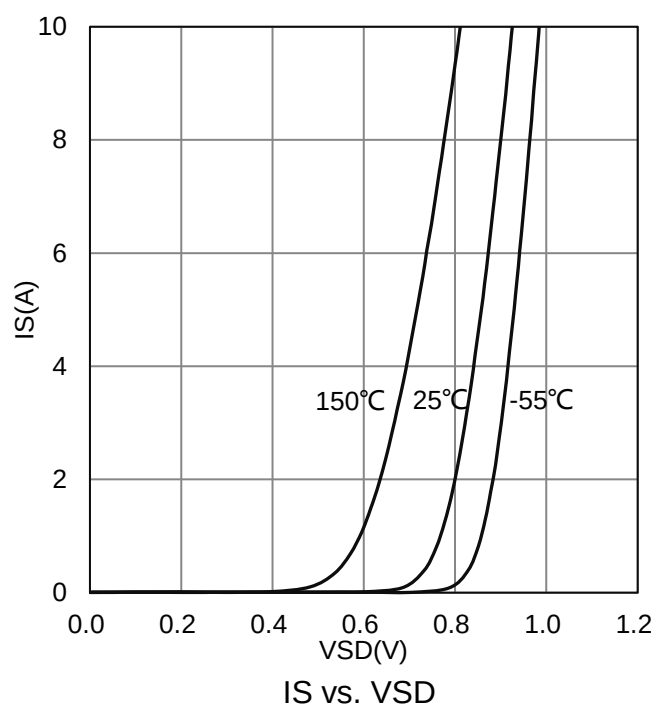
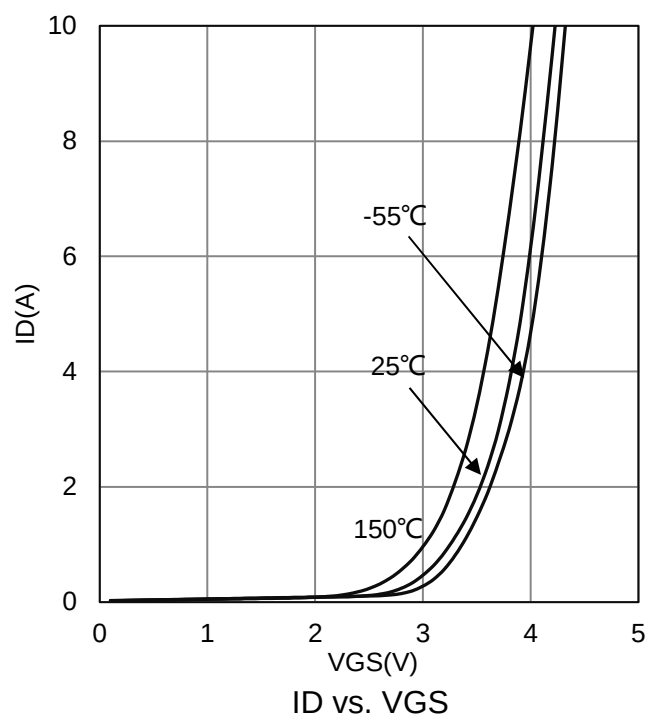
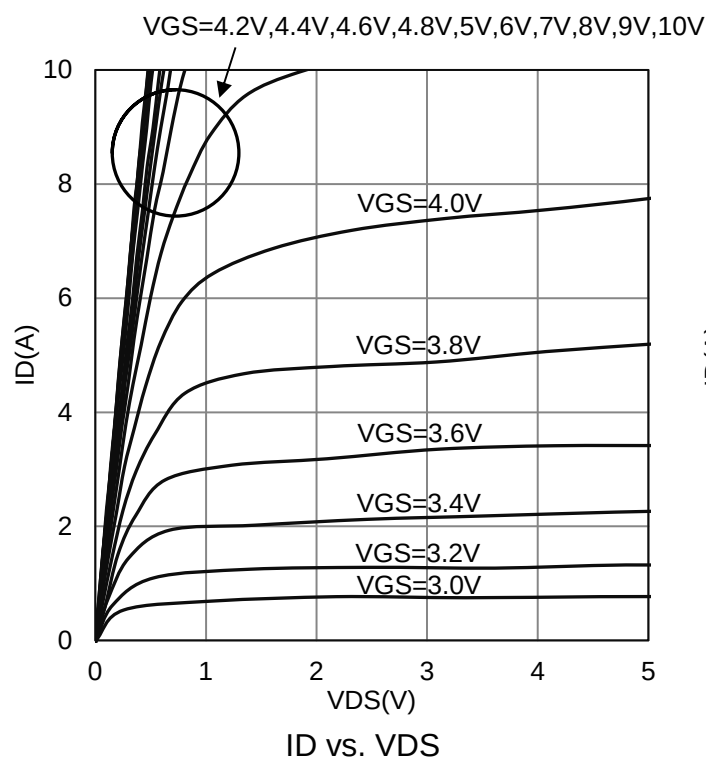


6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

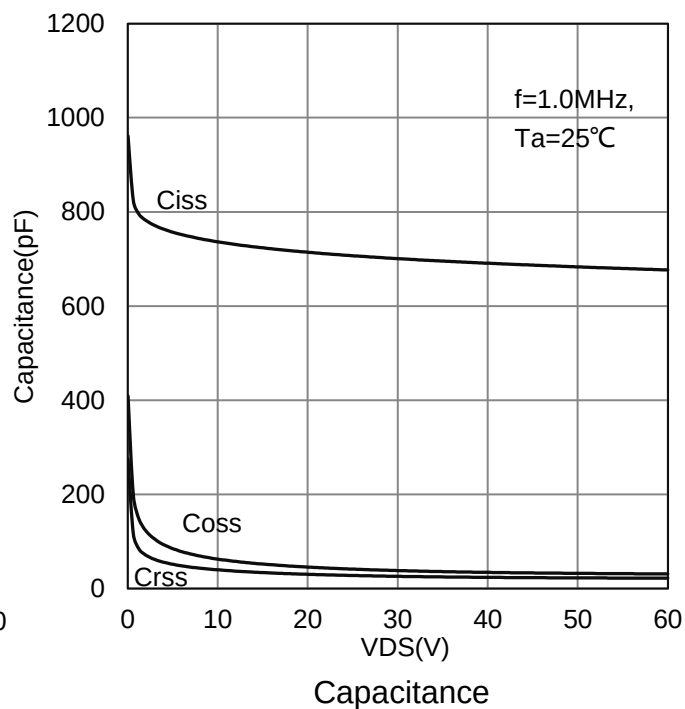
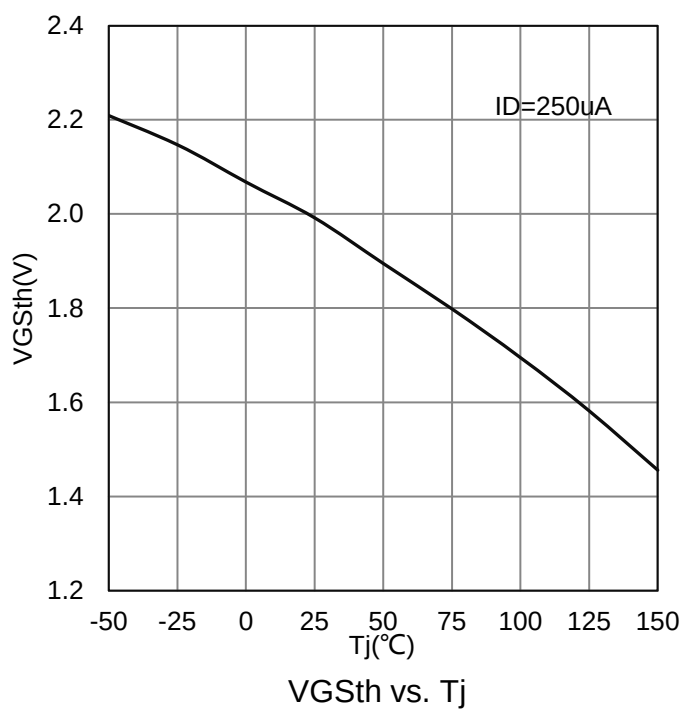
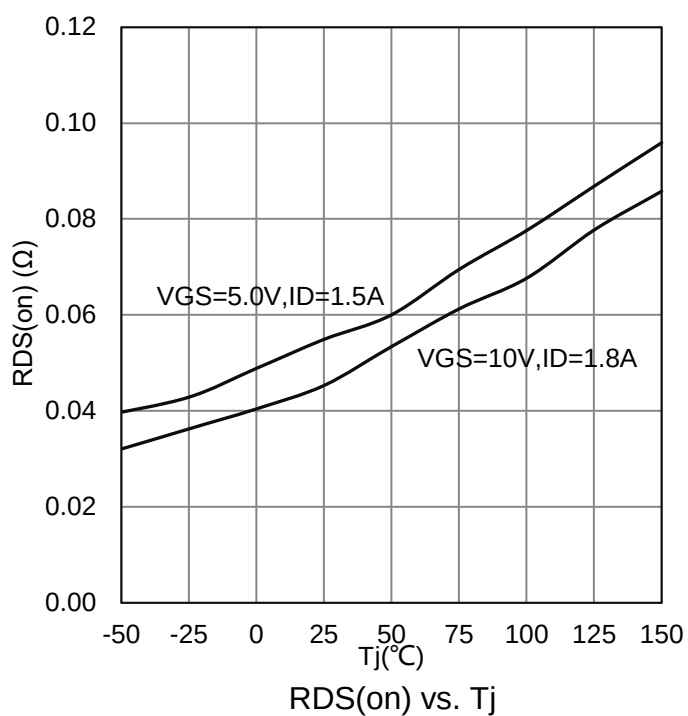
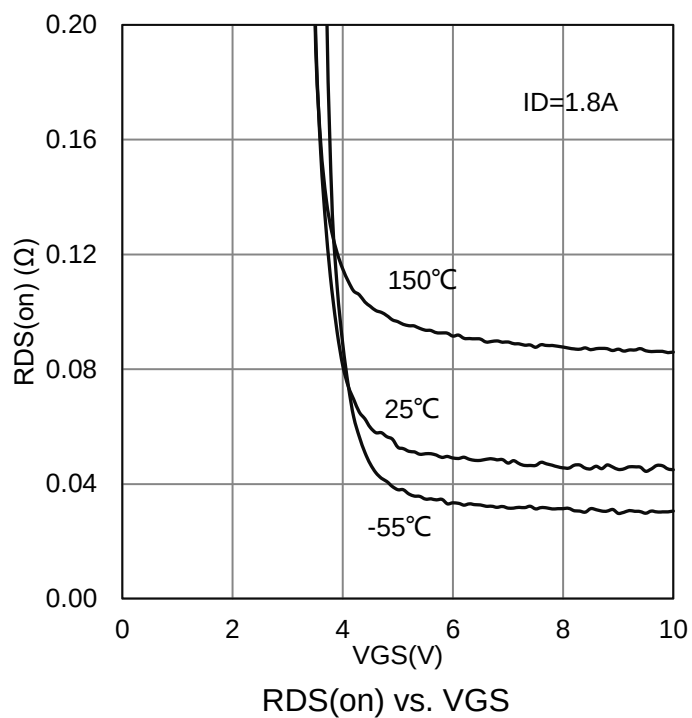
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Static					
Drain–Source Breakdown Voltage (VGS = 0 V, ID = 250 μ A)	VBRDSS	60	-	-	V
Gate-Source Threshold Voltage (VDS = VGS, ID = 250 μ A)	VGS(th)	1	2	3	V
Gate-Body Leakage Current (VDS = 0 V, VGS = $\pm$ 20 V)	IGSS	-	-	$\pm$ 100	nA
Zero Gate Voltage Drain Current (VDS = 60 V, VGS = 0 V)	IDSS	-	-	1	μ A
Drain-Source On-Resistance(Note 3) (VGS = 10 V, ID = 1.8 A) (VGS = 5 V, ID = 1.5 A)	RDS(ON)	- -	- -	75 90	m Ω
Diode Forward Voltage (IS = 1 A, VGS = 0 V)	VSD	-	0.8	1.2	V
Dynamic					
Total Gate Charge	(VDS = 30 V, VGS = 10 V, ID = 1.8 A)	Qg	-	12.2	nC
Gate-Source Charge		Qgs	-	2.2	
Gate-Drain Charge		Qgd	-	3.4	
Input Capacitance	(VGS = 0 V, VDS = 30 V, f= 1MHz)	Ciss	-	700	pF
Output Capacitance		Coss	-	39	
Reverse Transfer Capacitance		Crss	-	26.5	
Turn-On Delay Time	(VDD = 20 V, RL = 20 Ω , ID = 1 A, VGEN = 10 V, RG = 1 Ω)	td(on)	-	7	ns
Rise Time		tr	-	2.4	
Turn-Off Delay Time		td(off)	-	21.5	
Fall Time		tf	-	2.4	

3. Pulse test: PW $\leq$ 300 μ s duty cycle $\leq$ 2%.

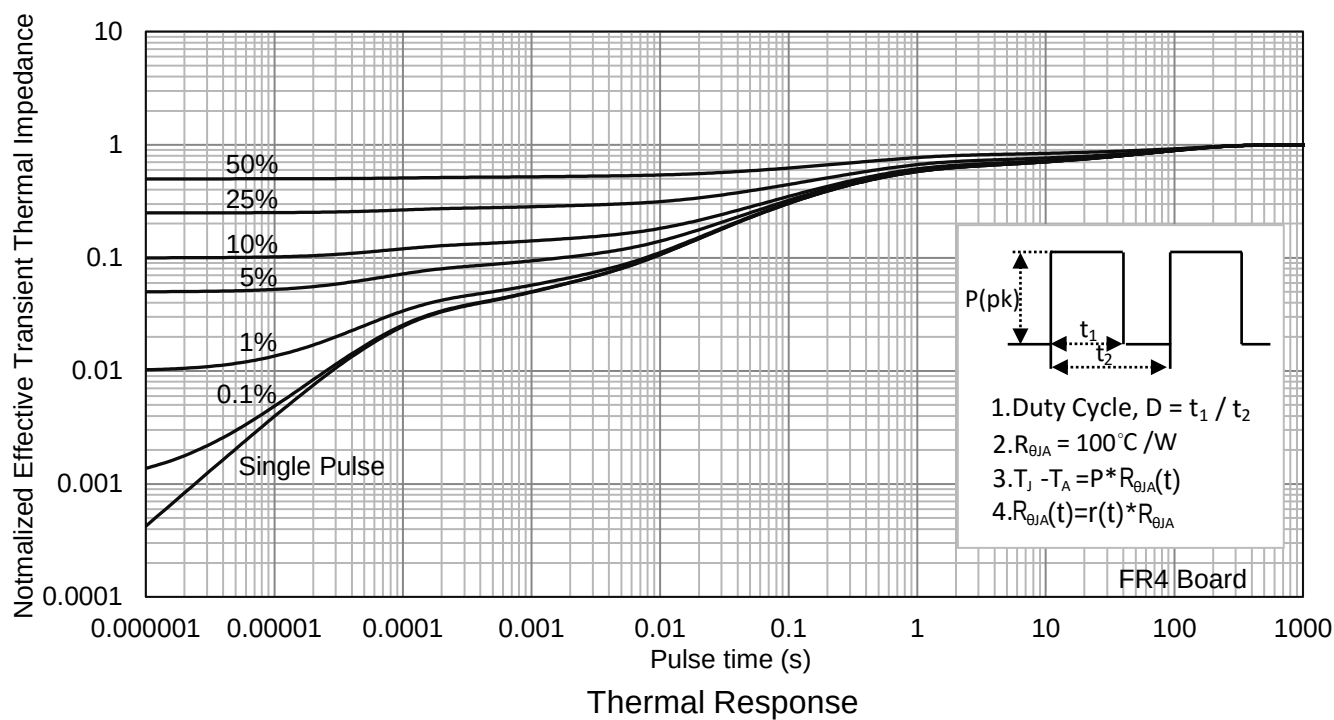
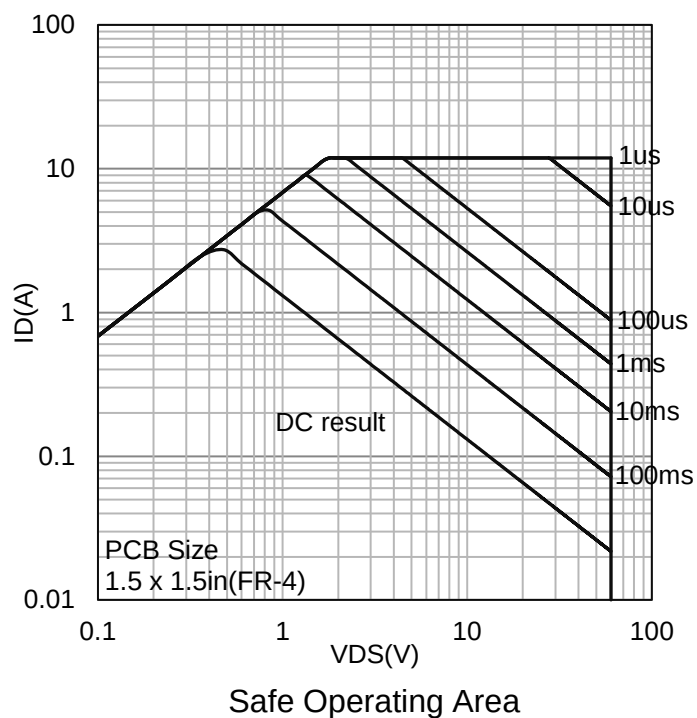
7. ELECTRICAL CHARACTERISTICS CURVES



7. ELECTRICAL CHARACTERISTICS CURVES(Con.)



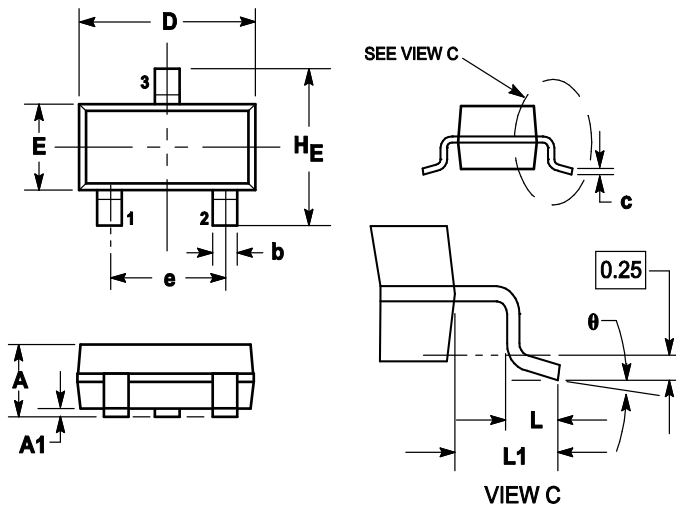
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8.OUTLINE AND DIMENSIONS

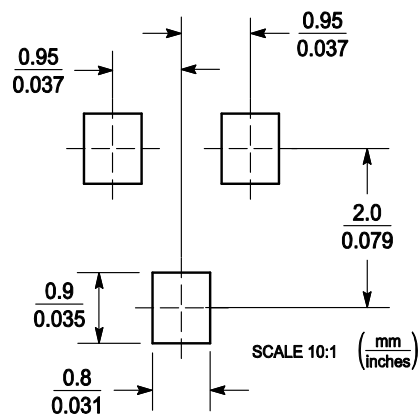
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H _E	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

9.SOLDERING FOOTPRINT



DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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